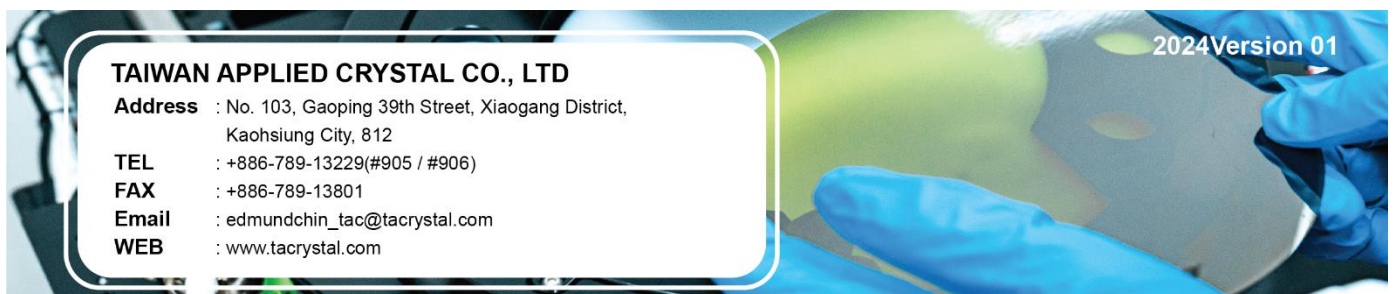


TAC 6" SiC 4H N-Type Specification

Grade	Dummy	Prime
Diameter	149.5-150.0 mm	149.5-150.0 mm
Polytype	4H	4H
Thickness	350 um ± 25 um	350 um ± 25 um
Wafer Orientation	4° toward <11-20> ± 0.5°	4° toward <11-20> ± 0.5°
MP	≤ 15/cm ²	≤ 0.2/cm ²
Resistivity	0.015-0.028 ohm · cm	0.015-0.024 ohm · cm
LTV	5 um	2.5 um
TTV	15 um	6 um
Bow	40 um	25 um
Warp	60 um	35 um
BPD	N/A	< 2000 /cm ²
TSD	N/A	< 100 /cm ²
TED	N/A	< 3000 /cm ²
EPD	N/A	< 5000 /cm ²
Roughness (Polish/CMP)	Ra<1 nm/Ra<0.5 nm	Ra<1 nm/Ra<0.2 nm
Si-face scratches (Cumulative length)	<150 mm	none
Packaging	Multi-wafer cassette or single wafer container (vacuum, no air leakage & damage)	Multi-wafer cassette or single wafer container (vacuum, no air leakage & damage)



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